

**TD3169**

## Capabilities Data Sheet

# Solar Array Bypass Diode

### Features

- Very Thin Construction
- Low leakage reverse current
- Low forward voltage drop
- Flexible leads for surface mount soldering or welding
- Die available with Ti-Pd-Ag or Al metallization
- Space Level Quality

**20 Volts**  
**2.0 Amps**

### Applications

- Bypass diode designed for Solar Cell protection
- Extreme Temperature Cycling environments
- Exposed Solar Array surface mount

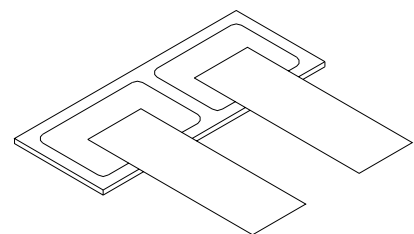
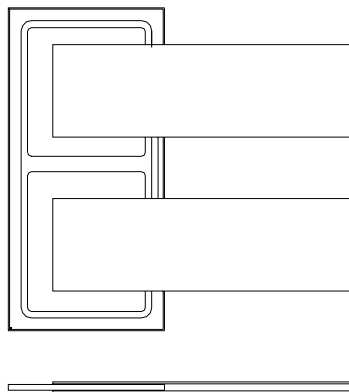
### Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	MAX	UNITS
IR	Reverse (Leakage) Current	VR = 5 Vdc	0.5	uAmps
VF1	Forward Voltage	IF = 2.0 A pulse test pw=300ms, d/c<2%	800	mVolts
VF2	Forward Voltage	IF = 2.0 A pulse test pw=300ms, d/c<2%	825	mVolts
VF3	Forward Voltage	IF = 2.0 A pulse test pw=300ms, d/c<2%	850	mVolts
BVR	Breakdown Voltage	IR = 100 uA	(min) 80	Volts

### Mechanical Outline

### Suggested QCI Testing

- Bond Pull
- Temperature Cycling
- High Temperature Reverse Bias



**Chip Dimensions**  
 6.4mm x 3.0mm x 250µm  
**Lead Configuration**  
 TBD